

Hironori Yoshioka

List of Publications by Year in descending order

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25
papers

535
citations

933447

10
h-index

713466

21
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26
all docs

26
docs citations

26
times ranked

414
citing authors

#	ARTICLE	IF	CITATIONS
1	Generation of very fast states by nitridation of the SiO ₂ /SiC interface. Journal of Applied Physics, 2012, 112, .	2.5	140
2	Accurate evaluation of interface state density in SiC metal-oxide-semiconductor structures using surface potential based on depletion capacitance. Journal of Applied Physics, 2012, 111, .	2.5	112
3	N-channel field-effect mobility inversely proportional to the interface state density at the conduction band edges of SiO ₂ /4H-SiC interfaces. AIP Advances, 2015, 5, .	1.3	57
4	High Breakdown Voltage ($\sim 1000\text{ V}$) Semi-Superjunction MOSFETs Using 600-V Class Superjunction MOSFET Process. IEEE Transactions on Electron Devices, 2005, 52, 2317-2322.	3.0	35
5	Effects of interface state density on 4H-SiC n-channel field-effect mobility. Applied Physics Letters, 2014, 104, 083516.	3.3	35
6	Characterization of very fast states in the vicinity of the conduction band edge at the SiO ₂ /SiC interface by low temperature conductance measurements. Journal of Applied Physics, 2014, 115, .	2.5	32
7	Quantum-confinement effect on holes in silicon nanowires: Relationship between wave function and band structure. Journal of Applied Physics, 2011, 109, 064318.	2.5	16
8	Characterization of SiO ₂ /SiC interface states and channel mobility from MOSFET characteristics including variable-range hopping at cryogenic temperature. AIP Advances, 2018, 8, .	1.3	16
9	Reduction of interface states by hydrogen treatment at the aluminum oxide/4H-SiC Si-face interface. AIP Advances, 2016, 6, .	1.3	15
10	Physics of SiC MOS interface and development of trench MOSFETs. , 2013, , .		14
11	Enhanced Drain Current of 4H-SiC MOSFETs by Adopting a Three-Dimensional Gate Structure. IEEE Transactions on Electron Devices, 2009, 56, 2632-2637.	3.0	12
12	Mobility oscillation by one-dimensional quantum confinement in Si-nanowire metal-oxide-semiconductor field effect transistors. Journal of Applied Physics, 2009, 106, 034312.	2.5	10
13	Novel magnetic phase transitions and magnetoresistance of GdMn ₂ Ge ₂ . Journal of Physics Condensed Matter, 2002, 14, L687-L693.	1.8	7
14	Theoretical investigation of the interface fluctuation causing low channel conductivity at SiO ₂ /SiC interfaces through the self-energy and average Green's function. AIP Advances, 2019, 9, 075306.	1.3	7
15	Bandgap shift by quantum confinement effect in $\sim 100\%$ Si-nanowires derived from threshold-voltage shift of fabricated metal-oxide-semiconductor field effect transistors and theoretical calculations. Journal of Applied Physics, 2011, 109, 064312.	2.5	6
16	(Invited) Interface Defects in C-face 4H-SiC MOSFETs: An Electrically-Detected-Magnetic-Resonance Study. ECS Transactions, 2017, 80, 147-153.	0.5	6
17	Accurate Characterization of Interface State Density of SiC MOS Structures and the Impacts on Channel Mobility. Materials Science Forum, 2014, 778-780, 418-423.	0.3	5
18	Novel Field-induced Magnetic Transitions of GdMn ₂ Ge ₂ . Journal of the Physical Society of Japan, 2003, 72, 3197-3203.	1.6	2

#	ARTICLE	IF	CITATIONS
19	Plastic deformation of single crystals with the C11b structure : Effect of the c/a axial ratio. Materials Research Society Symposia Proceedings, 2000, 646, 62.	0.1	1
20	Characterization of Interface State Density from Subthreshold Slope of MOSFETs at Low Temperatures (≈ 10 K). Materials Science Forum, 2015, 821-823, 745-748.	0.3	1
21	Determination of the interface between amorphous insulator and crystalline 4H-SiC in transmission electron microscope image by using convolutional neural network. AIP Advances, 2021, 11, 015101.	1.3	1
22	Field-induced magnetic transitions of exchange competing system GdMn ₂ Ge ₂ . Journal of Magnetism and Magnetic Materials, 2004, 272-276, 591-592.	2.3	0
23	Fabrication and Electronic Characteristics of Silicon Nanowire MOSFETs. Materials Research Society Symposia Proceedings, 2008, 1080, 1.	0.1	0
24	Improved On-Current of 4H-SiC MOSFETs with a Three-Dimensional Gate Structure. Materials Science Forum, 0, 615-617, 753-756.	0.3	0
25	Tight-binding study of size and geometric effects on hole effective mass of silicon nanowires. , 2010, , .		0